

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	569	ruthenium with Cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/05 14:17
S2	704	ruthenium with ((chemical vapor deposition) or cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/31 16:21
S3	59	ruthenium with ((chemical vapor deposition) or cvd) with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/05 14:19
S4	0	S3 and (iodine with plasma with (treat\$4 or etch\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/31 16:25
S5	2	("20020070194").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 10:59
S6	0	(ethyl iodide) with plasma with (etch\$4 or treat\$4 or clean\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:10
S7	0	(ethyl iodide) with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:03
S8	1	((ethyl or propyl) iodine) with plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:05
S9	59	ruthenium with ((chemical vapor deposition) or cvd) with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 12:07
S10	0	S9 and ((ethyl iodine) with plasma with (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:11

S11	0	S9 and (((ethyl or propyl) (I or iodine)) with plasma with (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:40
S12	21	(("6605549") or ("6638859") or ("6413864") or ("6468907") or ("6593236") or ("6613695") or ("6605735") or ("6284652") or ("6074945")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 11:16
S13	0	S9 and ((I or iodine) with plasma with (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:41
S14	5301	(((I or iodine) with plasma) same (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:42
S15	3629	((I or iodine) with plasma with (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:45
S16	1521293	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 11:31
S17	1259	S16 and ((I or iodine) with plasma with (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:45
S18	83	S16 and (iodine with plasma with (etch\$4 or treat\$4 or clean\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 11:46
S19	5	S16 and (iodine with plasma with (etch\$4 or treat\$4 or clean\$4) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/02 12:06
S20	10520	438/681,686,653,654,677,687,674, 680,622,625,758,780,767,769,775, 788,789.ccis.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:28

S21	7	S20 and (ruthenium with ((chemical vapor deposition) or cvd) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 11:32
S23	1521293	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:36
S24	10520	438/681,686,653,654,677,687,674, 680,622,625,758,780,767,769,775, 788,789.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 11:31
S25	7	S24 and (ruthenium with ((chemical vapor deposition) or cvd) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 11:32
S26	6	S25 and ((ru or ruthenium) with thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 11:33
S27	10520	438/681,686,653,654,677,687,674, 680,622,625,758,780,767,769,775, 788,789.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:28
S28	0	S27 and (plasma with surfactant with (iodine or lead or tin or gallium or indium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:39
S29	0	S27 and (plasma same (surfactant with (iodine or lead or tin or gallium or indium)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:40
S30	2	S27 and plasma and (surfactant with (iodine or lead or tin or gallium or indium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:44
S31	403	"16" and plasma and (surfactant with (iodine or lead or tin or gallium or indium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:45

S32	89	semiconductor and plasma and (surfactant with (iodine or lead or tin or gallium or indium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:45
S33	8	semiconductor and plasma and (surfactant with (iodine or lead or tin or gallium or indium)) and ruthenium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:48
S34	127483	semiconductor and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:48
S35	8	S34 and (surfactant with (iodine or lead or tin or gallium or indium)) and ruthenium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:49
S36	8	S34 and (surfactant with (iodine or lead or tin or gallium or indium)) and ruthenium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:51
S37	290	S34 and (spec\$4 with (iodine or lead or tin or gallium or indium)) and ruthenium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:53
S38	94	S34 and (spec\$4 with (iodine or lead or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 14:55
S39	30	S34 and (species with (iodine or lead or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:01
S40	356	S34 and (species with (iodine or I or Pb or Sn or Ga or In or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:02
S41	154	S34 and ((species with (iodine or I or Pb or Sn or Ga or In or tin or gallium or indium) with dielectric) same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:03

S42	113	S34 and ((species with (iodine or I or Pb or Sn or Ga or tin or gallium or indium) with dielectric) same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:08
S43	214	S34 and (species with (iodine or I or Pb or Sn or Ga or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:11
S44	0	S34 and (species with surfactant with (iodine or I or Pb or Sn or Ga or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:06
S45	0	S34 and (species with (chemical enhancer) with (iodine or I or Pb or Sn or Ga or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:07
S46	0	S43 and (species with (chemical enhancer) with (iodine or I or Pb or Sn or Ga or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:07
S47	48	S34 and (species with (iodine or I or Pb or Sn or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:12
S48	20	S34 and (species with (iodine or Pb or tin or gallium or indium) with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/03 15:12
S49	1596989	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:37
S50	74527	S49 and (substrate with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:38
S51	4	S50 and (iodine with plasma with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:43

S52	0	S51 and ((ru or ruthenium) with cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:43
S53	5	S49 and (iodine with plasma with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:44
S54	0	S53 and ((ru or ruthenium) with cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:44
S55	812	S49 and ((ru or ruthenium) with cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:44
S56	0	S55 and (iodine with plasma with dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/12/09 12:44
S57	1476	427/532,535.ccls. or 438/650,686. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/05 14:18
S58	71	S57 and (ruthenium with ((chemical vapor deposition) or cvd))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/05 14:20
S59	0	S58 and (iodine near3 precursor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/05 14:20
S60	4	S58 and iodine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/05 14:26
S61	0	S60 and (substrate near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/06 08:35

S62	4	(("6365486") or ("6146941")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/06 08:35
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